

L Number	Hits	Search Text	DB	Time stamp
1	28	250/49\$.ccls. and ion adj beam and align\$5 and mask and slit and density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
2	19	(250/49\$.ccls. and ion adj beam and align\$5 and mask and slit and density) and density with ion	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
3	54	250/49\$.ccls. and ion adj beam and align\$5 and mask and slit	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
4	45	(250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
5	1	((250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole same density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
6	7	((250/49\$.ccls. and ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
7	38	250/\$.ccls. and ion adj beam and align\$5 and mask and slit and density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
8	375	ion adj beam and align\$5 and mask and slit	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
9	88	(ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
10	77	((ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
11	304	(ion adj beam and align\$5 and mask and slit) and plate\$5	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
12	11	((ion adj beam and align\$5 and mask and slit) and ((liquid adj crystal adj display) LCD)) and plate\$5) and plate\$5 same hole same density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
13	97	((ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole	USPAT; EPO; JPO; DERWENT	2004/09/08 11:04
14	83	((ion adj beam and align\$5 and mask and slit) and plate\$5) and plate\$5 same hole) and density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
15	364	ion adj beam and align\$5 and mask and slit and (substrate wafer)	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
16	12	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and hole with density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
17	39	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and hole same density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
18	39	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and hole same density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
19	26	(ion adj beam and align\$5 and mask and slit and (substrate wafer)) and aperture same density	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
20	92	250/49\$.ccls. and beam same density and mask and slit	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05
21	33	250/49\$.ccls. and beam same density same (hole aperture) and mask and slit	USPAT; EPO; JPO; DERWENT	2004/09/08 11:05